

Isc N-Channel MOSFET Transistor

TK31N60W

• FEATURES

- Low drain-source on-resistance: $R_{DS(ON)} = 0.073 \Omega$ by used to Super Junction Structure : DTMOS
- Easy to control Gate switching
- Enhancement mode: $V_{th} = 2.7$ to 3.7 V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• Applications

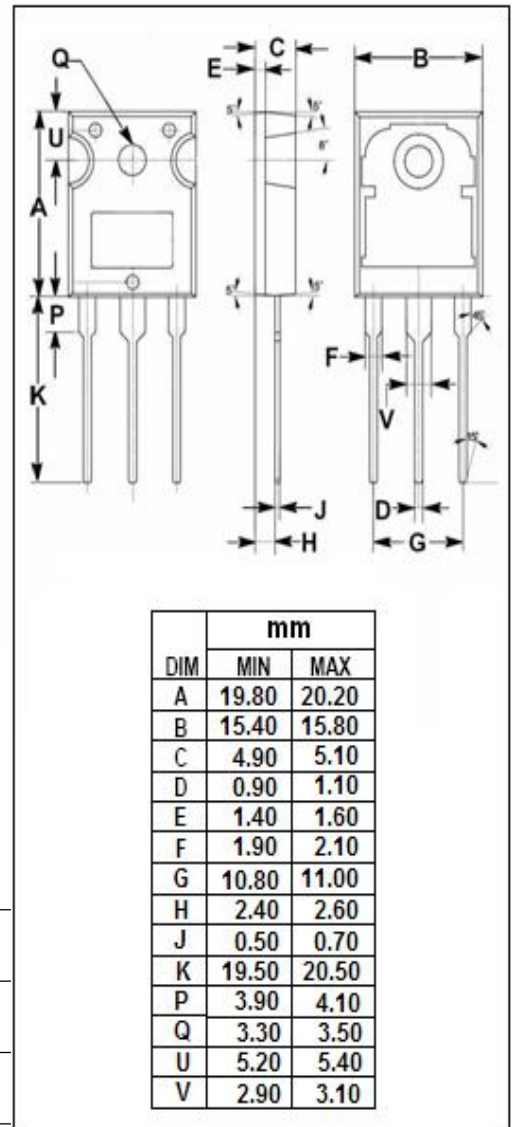
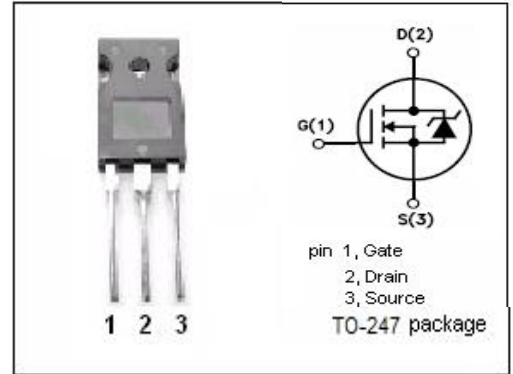
- Switching Voltage Regulators

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	600	V
V_{GSS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous	30.8	A
I_{DM}	Drain Current-Single Pulsed	123	A
P_D	Total Dissipation	230	W
T_{ch}	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.54	$^\circ C/W$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	50	$^\circ C/W$



Isc N-Channel MOSFET Transistor

TK31N60W

ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 10mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = 10V; I _D =1.5mA	2.7		3.7	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =15.4A			88	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0V			±1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 600V; V _{GS} = 0V			10	μA
V _{SD}	Diode forward voltage	I _{SD} =30.8A, V _{GS} = 0 V			1.7	V